

Hex Schmitt Trigger Inverter in Plastic Small-Outline Package (SOIC)

Rev 1.0 17/02/2023

Description

The MM74C14M Hex Schmitt Trigger is a monolithic complementary MOS (CMOS) integrated circuit constructed with N-channel and P-channel enhancement transistors. The positive and negative going threshold voltages, V_{T+} and V_{T-} , show low variation with respect to temperature (typ. 0.0005 V/°C at V_{CC} = 10V), and hysteresis, V_{T+} - $V_{T-} \geq 0.2$ V_{CC} is guaranteed. All inputs are protected from damage due to static discharge by diode clamps to V_{CC} and GND.

Ordering Information

The following part suffixes apply:

MM74C14M - 14 Lead Plastic SOIC Package

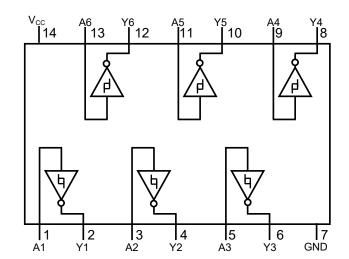
Function Table

INPUT	OUTPUT	
A	Y	
L H	H	

Features:

- Wide supply voltage range: 3V to 15V
- High noise immunity: 0.70 V_{CC} (typ.)
- Low power TTL compatibility:
 - o 0.40 V_{CC} (typ.)
 - o 0.20 V_{CC} (guaranteed)
- Hysteresis:
 - o 0.40 V_{CC} (typ.)
 - o 0.20 V_{CC} (guaranteed).

Schematic & Connection Diagram



Absolute Maximum Ratings¹

PARAMETER	SYMBOL	VALUE	UNIT	
Voltage at any input pin	V _{IN}	-0.3 to V _{CC} + 0.3	V	
Voltage at any output pin	V _{OUT}	-0.3 to V _{CC} + 0.3	V	
Operating V _{CC} range	V _{CC}	3 to 15	V	
Absolute maximum V _{CC}	V _{CC(MAX)}	18	V	
Maximum Power Dissipation	P _D	700	mW	
Operating Temperature Range	T _A	-40 to +85	°C	
Storage Temperature Range	T _{STG}	-65 to +150	°C	
Lead Temperature (Soldering, 10 seconds)	T _L	260	°C	

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability.





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DC Electrical Characteristics T_A = -40 to +85°C unless otherwise stated

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CMOS TO CMOS						
Positive Going Threshold Voltage		$V_{CC} = 5V$	3.0	3.6	4.3	V
	V_{T+}	V _{CC} = 10V	6.0	6.8	8.6	V
		V _{CC} = 15V	9.0	10.0	12.9	V
Negative Going Threshold Voltage		$V_{CC} = 5V$	0.7	1.4	2.0	V
	V _{T-}	V _{CC} = 10V	1.4	3.2	4.0	V
		V _{CC} = 15V	2.1	5.0	6.0	V
Hysteresis		$V_{CC} = 5V$	1.0	2.2	3.6	V
	$V_{T+} - V_{T-}$	V _{CC} = 10V	2.0	3.6	7.2	V
		V _{CC} = 15V	3.0	5.0	10.8	V
Logical "1" Output Voltage	V _{OUT(1)}	$V_{CC} = 5V, I_{O} = -10\mu A$	4.5	-	-	V
	V OUT(1)	$V_{CC} = 10V, I_{O} = -10\mu A$	9.0	-	-	V
Logical "0" Output Voltage	V _{OUT(0)}	$V_{CC} = 5V, I_{O} = 10\mu A$	-	-	0.5	V
	V OUT(0)	$V_{CC} = 10V, I_{O} = 10\mu A$	-	-	1.0	V
Logical "1" Input Current	I _{IN(1)}	$V_{CC} = 15V, V_{IN} = 15V$	-	0.005	1.0	μA
Logical "0" Input Current	I _{IN(0)}	$V_{CC} = 15V, V_{IN} = 0V$	-1.0	-0.005	-	μA
Supply Current	I _{cc}	$V_{CC} = 15V, V_{IN} = 0V/15V$	-	0.05	15	μA
Supply Current ²		$V_{CC} = 5V, V_{IN} = 2.5V$	-	20	-	μA
	I _{CC}	$V_{CC} = 10V, V_{IN} = 5V$	-	200	-	μA
		$V_{CC} = 15V, V_{IN} = 7.5V$	-	600	-	μA
CMOS/LPTTL INTERFACE						
Logical "1" Input Voltage	V _{IN(1)}	$V_{CC} = 5V$	4.3	-	-	V
Logical "0" Input Voltage	V _{IN(0)}	$V_{CC} = 5V$	-	-	0.7	V
Logical "1" Output Voltage	V _{OUT(1)}	$V_{CC} = 4.75V, I_{O} = -360\mu A$	2.4	-	-	V
Logical "0" Output Voltage	V _{OUT(0)}	V_{CC} =4.75V, I_{O} = 360 μ A	-	-	0.4	V
OUTPUT DRIVE CURRENT $T_A = 25^{\circ}C$						
Output Source Current (P-Channel)	I _{SOURCE}	$V_{CC} = 5V, V_{OUT} = 0V$	-1.75	-3.3	-	mA
	SOURCE	$V_{CC} = 10V, V_{OUT} = 0V$	-8.0	-15	-	mA
Output Source Current (N-Channel)	I _{SINK}	$V_{CC} = 5V, V_{OUT} = V_{CC}$	1.75	3.6	-	mA
		$V_{CC} = 10V$, $V_{OUT} = V_{CC}$	8.0	16	-	mA
DYNAMIC ELECTRICAL CHARACTE	RISTICS ³ T _A = 25	°C, C _L = 50pF unless oth	erwise	stated		
$ \begin{array}{c c} \text{Propagation Delay} & & & t_{\text{PD0},} \\ \text{from Input to Output} & & & t_{\text{PD1}} \\ \end{array} $	V _{CC} = 5V	-	220	400	ns	
		V _{CC} = 10V	-	80	200	ns
Input Capacitance	C _{IN}	Any Input	-	5.0	-	pF
Power Dissipation Capacitance ⁴	C _{PD}	Per Gate	-	20	-	pF

^{2.} Only one of the six inputs is at $\frac{1}{2}$ V_{CC}; the others are either at V_{CC} or GND. 3. Not production tested in die form, characterized by chip design.



^{4.} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.



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Typical Characteristics

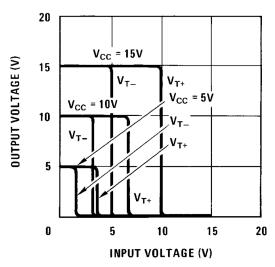


Figure 1 – Transfer Characteristics

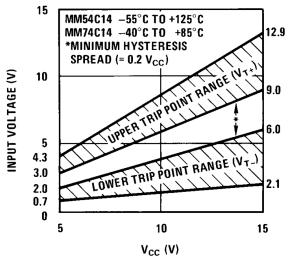


Figure 2 – Guaranteed Trip Point Range

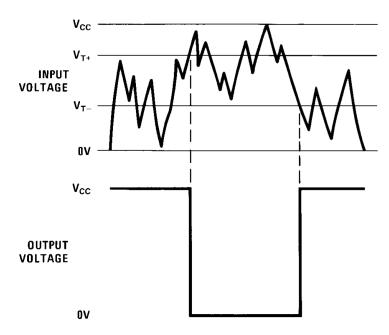


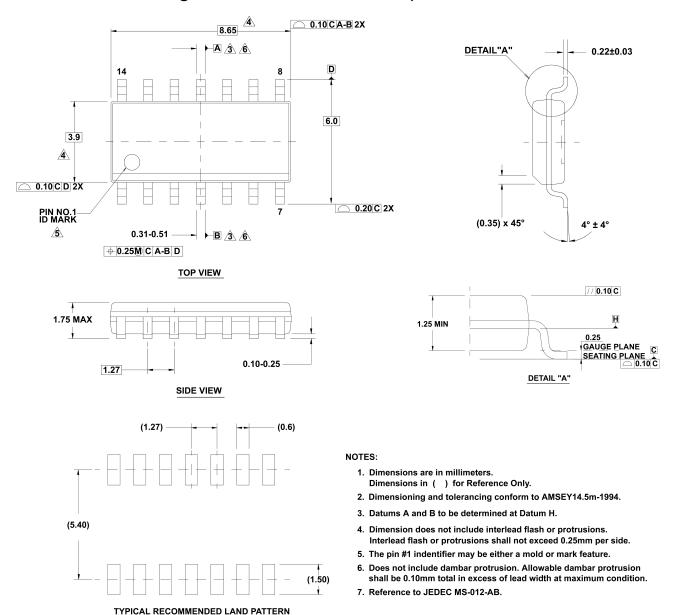
Figure 3 - Waveform





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SOIC 14 - Package Dimensions and Footprint



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